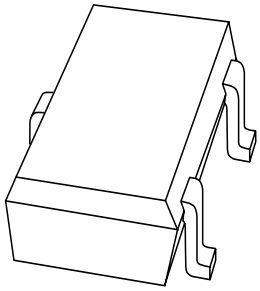
DATA SHEET



2PB1219A
PNP general purpose transistor

Product data sheet
Supersedes data of 1997 Mar 25

1999 Apr 12

NXP founded by Philips

PNP general purpose transistor 2PB1219A

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 50 V)
- Low collector-emitter saturation voltage (max. 600 mV).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT323; SC70 plastic package.
NPN complement: 2PD1820A.

MARKING

TYPE NUMBER	MARKING CODE(1)
2PB1219AQ	D∗Q
2PB1219AR	D∗R
2PB1219AS	D∗S

Note

1. ∗ = - : Made in Hong Kong.
   ∗ = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

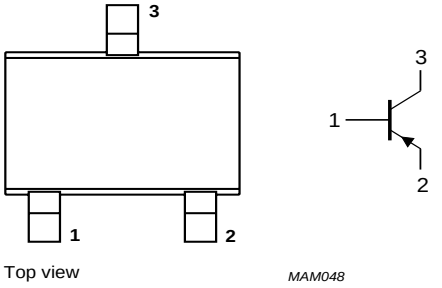


Fig.1 Simplified outline (SOT323; SC70) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	−60	V
V_{CEO}	collector-emitter voltage	open base	–	−50	V
V_{EBO}	emitter-base voltage	open collector	–	−5	V
I_C	collector current (DC)		–	−500	mA
I_{CM}	peak collector current		–	−1	A
I_{BM}	peak base current		–	−200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	200	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Refer to SOT323; SC70 standard mounting conditions.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Refer to SOT323; SC70 standard mounting conditions.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

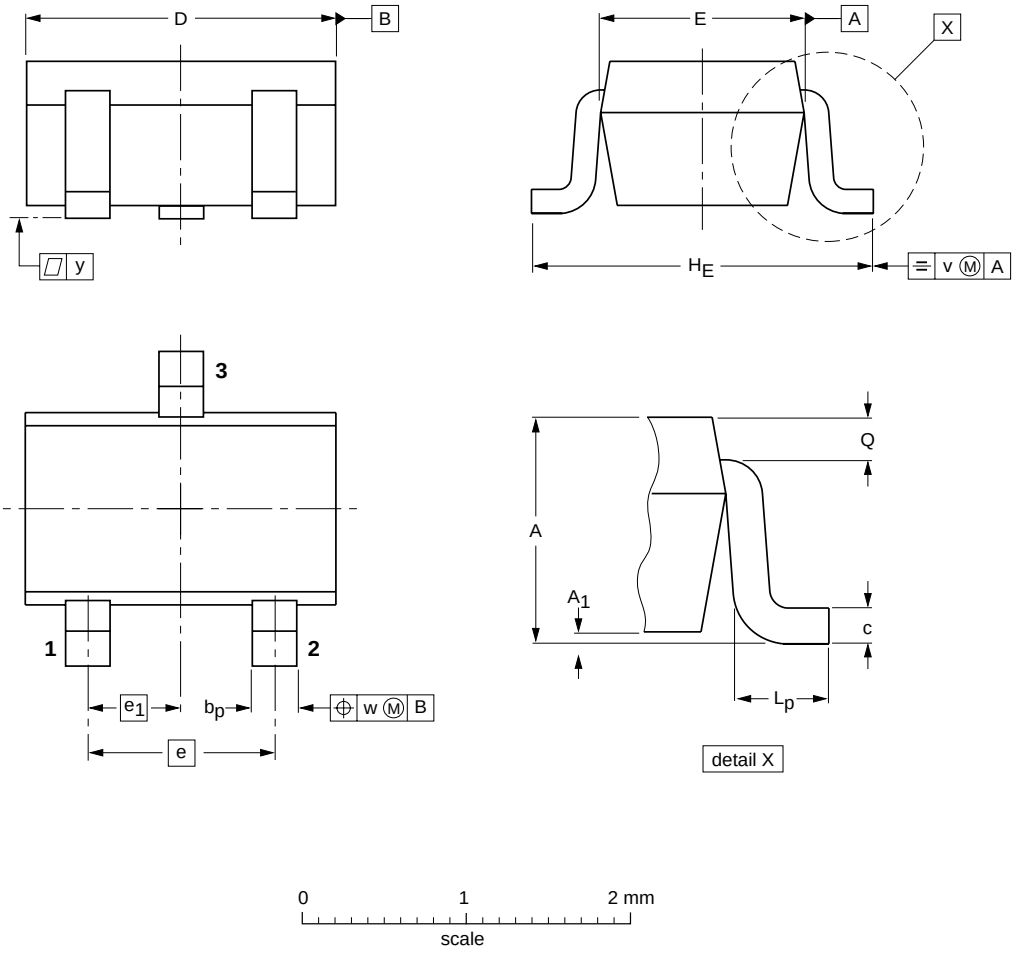
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = −20 V	−	−100	nA
		I_E = 0; V_{CB} = −20 V; T_j = 150 °C	−	−5	μA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = −4 V	−	−100	nA
h_{FE}	DC current gain	I_C = −150 mA; V_{CE} = −10 V; note 1			
	2PB1219AQ		85	170	
	2PB1219AR		120	240	
	2PB1219AS		170	340	
h_{FE}	DC current gain	I_C = −500 mA; V_{CE} = −10 V; note 1	40	−	
V_{CEsat}	collector-emitter saturation voltage	I_C = −300 mA; I_B = −30 mA; note 1	−	−600	mV
V_{BEsat}	base-emitter saturation voltage	IC = −300 mA; IB = −30 mA; note 1	−	−1.5	V
C_c	collector capacitance	I_E = i_e = 0; V_{CB} = −10 V; f = 1 MHz	−	15	pF
f_T	transition frequency	I_C = 50 mA; V_{CE} = −10 V;			
	2PB1219AQ	f = 100 MHz; note 1	100	−	MHz
	2PB1219AR		120	−	MHz
	2PB1219AS		140	−	MHz

Note

1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

DISCLAIMERS

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

Contact information

For additional information please visit: **http://www.nxp.com**
For sales offices addresses send e-mail to: **salesaddresses@nxp.com**

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands 115002/00/03/pp6 Date of release: 1999 Apr 12 Document order number: 9397 750 05589

founded by

PHILIPS

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9